

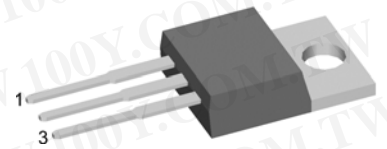
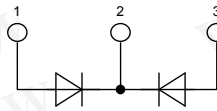
HiPerFRED²

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DPG 30 C 200 PB

$$\begin{aligned} V_{RRM} &= 200 \text{ V} \\ I_{FAV} &= 2 \times 15 \text{ A} \\ t_{rr} &= 35 \text{ ns} \end{aligned}$$



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- Housing: TO-220
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

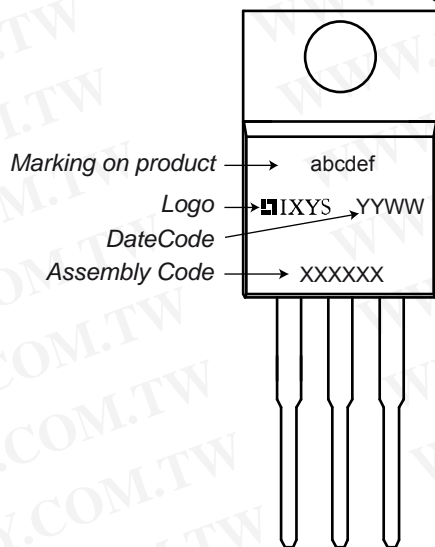
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{vj} = 25^\circ\text{C}$			200	V
I_R	reverse current	$V_R = 200\text{V}$ $T_{vj} = 25^\circ\text{C}$			1	μA
		$V_R = 200\text{V}$ $T_{vj} = 150^\circ\text{C}$			0.08	mA
V_F	forward voltage	$I_F = 15\text{A}$ $T_{vj} = 25^\circ\text{C}$			1.26	V
		$I_F = 30\text{A}$			1.51	V
		$I_F = 15\text{A}$ $T_{vj} = 150^\circ\text{C}$			1.01	V
		$I_F = 30\text{A}$			1.29	V
I_{FAV}	average forward current	rectangular $d = 0.5$ $T_c = 140^\circ\text{C}$			15	A
V_{FO}	threshold voltage	} for power loss calculation only $T_{vj} = 175^\circ\text{C}$			0.69	V
r_F	slope resistance				18	m Ω
R_{thJC}	thermal resistance junction to case				1.70	K/W
T_{vj}	virtual junction temperature		-55		175	$^\circ\text{C}$
P_{tot}	total power dissipation	$T_c = 25^\circ\text{C}$			90	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}$ (50 Hz), sine $T_{vj} = 45^\circ\text{C}$			240	A
I_{RM}	max. reverse recovery current	$T_{vj} = 25^\circ\text{C}$			3	A
		$I_F = 15 \text{ A}; V_R = 130 \text{ V}$ $T_{vj} = 125^\circ\text{C}$			6.5	A
t_{rr}	reverse recovery time	$-di_F/dt = 200 \text{ A}/\mu\text{s}$ $T_{vj} = 25^\circ\text{C}$			35	ns
		$T_{vj} = 125^\circ\text{C}$			55	ns
C_j	junction capacitance	$V_R = 150 \text{ V}; f = 1 \text{ MHz}$ $T_{vj} = 25^\circ\text{C}$			20	pF

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per pin ¹⁾			35	A
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
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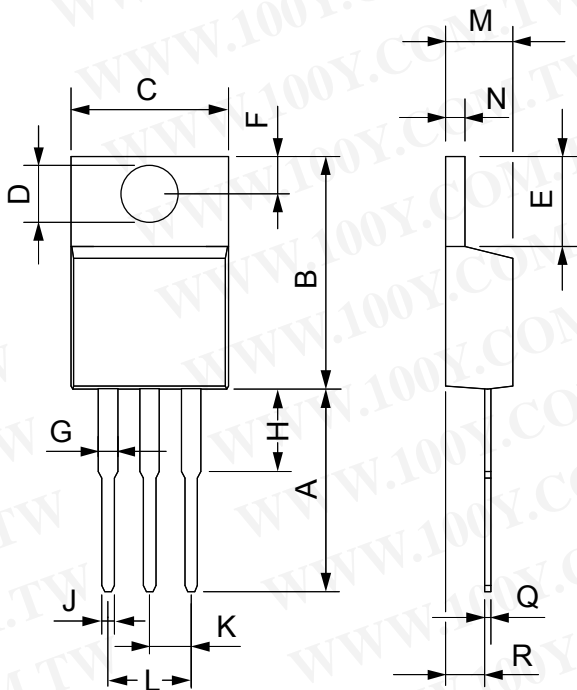
Product Marking

Part number

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 30 = Current Rating [A]
- C = Common Cathode
- 200 = Reverse Voltage [V]
- PB = TO-220AB (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPG 30 C 200 PB	DPG30C200PB	Tube	50	505804

Similar Part	Package	Voltage Class
DPG30C200PC	TO-263AB (D2Pak)	200
DPG30C200HB	TO-247AD (3)	200

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

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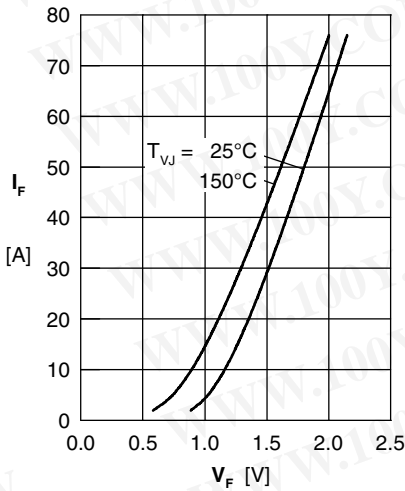


Fig. 1 Forward current I_F vs. V_F

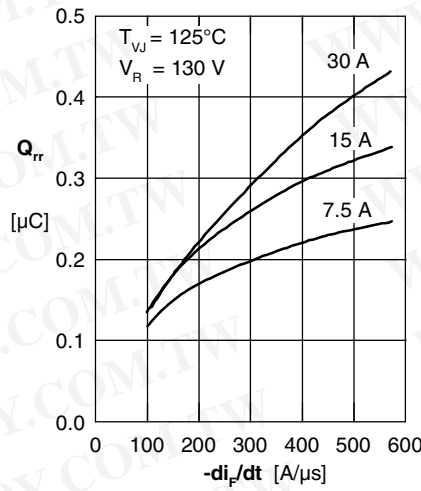


Fig. 2 Typ. reverse recovery charge Q_{rr} versus $-di_F/dt$

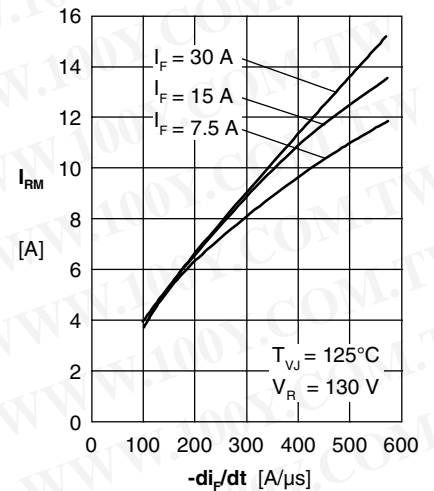


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

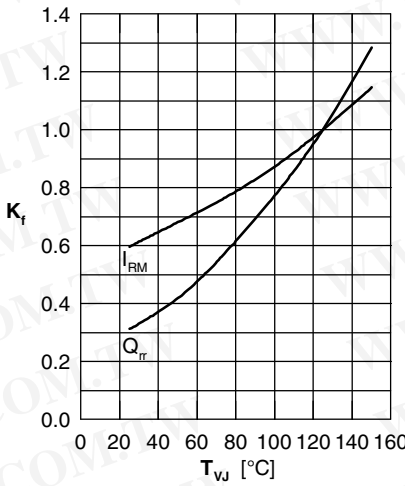


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

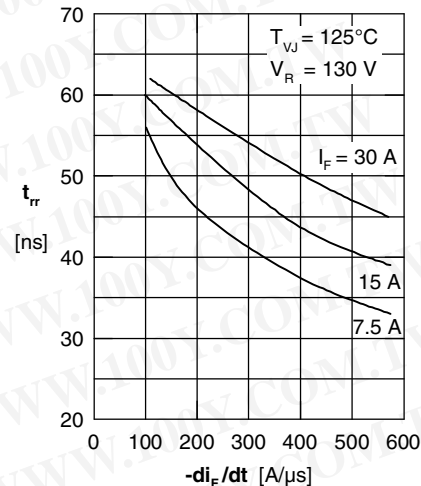


Fig. 5 Typ. recovery time t_{rr} vs. $-di_F/dt$

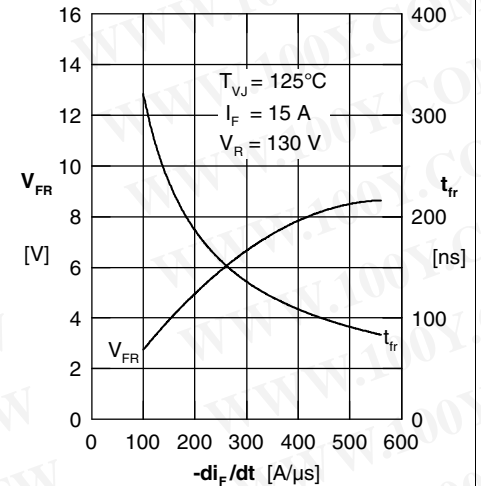


Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt

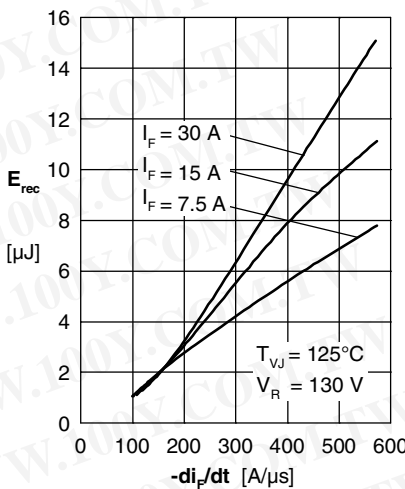


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

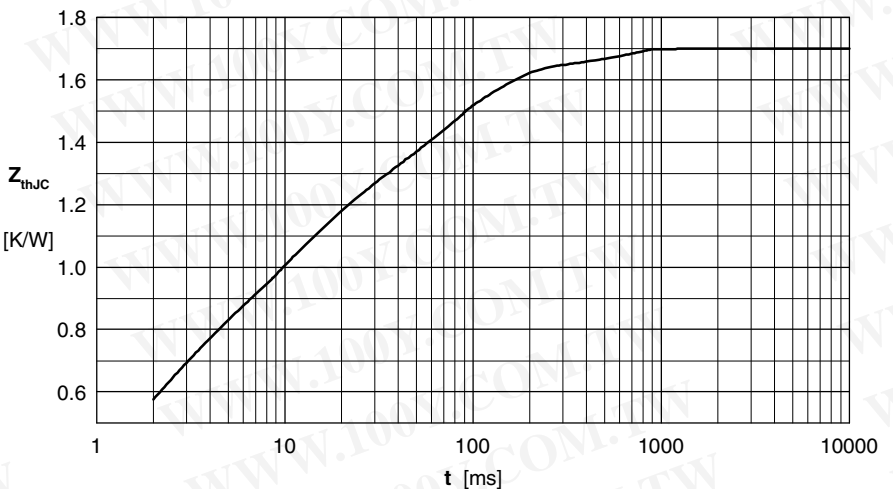


Fig. 8 Transient thermal resistance junction to case